



Solid State Devices, Inc.

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SFT5094 and SFT5096 Series

1 AMP, 500 Volts High Voltage PNP Transistor

DESIGNER'S DATA SHEET

Part Number / Ordering Information ^{1/}

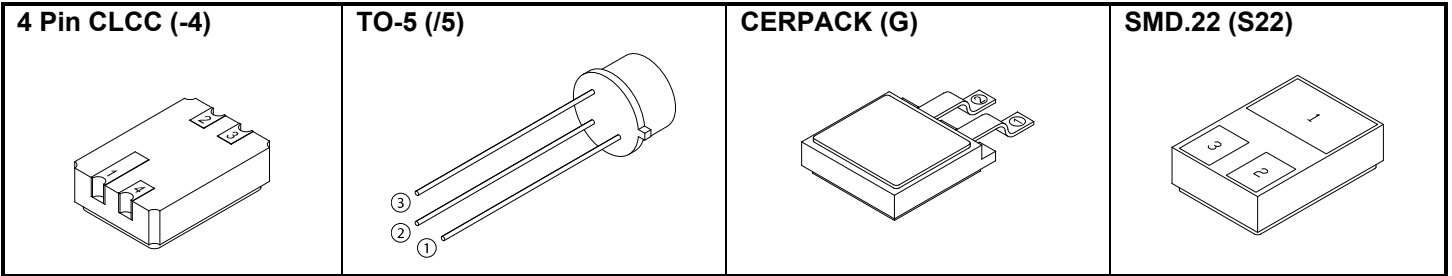
SFT5094
 SFT5096

Screening ^{2/} = No Screening
 TX = TX Level
 TXV = TXV Level
 S = S Level

Package ^{3/} -4 = 4 Pin CLCC
 /5 = TO-5
 G = CERPACK
 S22 = SMD.22

- Features:**
- BV_{CER} to 500 Volts
 - Low Leakage at High Temperature
 - High Linear Gain, Low Saturation Voltage
 - 200°C Operating Temperature
 - Gold Eutectic Die Attach
 - TX, TXV, S-Level Screening Available
 - Designed for Complementary Use with SFT5015
 - Replacement for 2N5094 and 2N5096 with Lower Thermal Resistance
 - Available with TO-5, Cerpack, CLCC, and SMD.22 Cases

Maximum Ratings ^{4/}	Symbol	SFT5094	SFT5096	Units
Collector – Emitter Voltage (R _{BE} = 1kΩ)	V _{CEO} V _{CER}	350 450	400 500	Volts Volts
Collector – Base Voltage	V _{CBO}	450	500	Volts
Emitter – Base Voltage	V _{EBO}	6		Volts
Collector Current	I _C	1.0		Amps
Base Current	I _B	0.5		Amps
Total Power Dissipation (T _C = 25°C) Derate above T _C = 25°C (T _A = 25°C)	P _D	1.0 0.4 5.7		Watts Watts mW /°C
Operating & Storage Temperature	T _J & T _{STG}	-65 to +200		°C
Maximum Thermal Resistance (Junction to Case)	R _{θJC}	4 Pin CLCC TO-5 CERPACK SMD.22	175 30 9 9	°C/W °C/W °C/W
Maximum Thermal Resistance (Junction to Ambient)	R _{θJA}	4 Pin CLCC TO-5 CERPACK SMD.22	440 --- 440 440	°C/W °C/W °C/W



NOTES: 1/ For Ordering Information, Price, Operating Curves, and Availability Contact Factory.
 2/ Screened to MIL-PRF-19500.
 3/ For Package Outlines, See Figure 1.
 4/ Unless Otherwise Specified, Maximum Ratings/Electrical Characteristics at 25°C.



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**SFT5094 and SFT5096
 Series**

Electrical Characteristics ^{4/}	Symbol	Min	Max	Units	
Collector – Emitter Breakdown Voltage * (I _C = 5 mA) (I _C = 100 μA, R _{BE} = 1k Ω)	BV_{CEO}	SFT5094 350	SFT5096 400	—	Volts
	BV_{CER}	450	500	—	
Collector – Base Breakdown Voltage * (I _C = 100 μA)	BV_{CBO}	450	500	—	Volts
Emitter – Base Breakdown Voltage (I _E = 50 μA)	BV_{EBO}	6	—	—	Volts
Collector Cutoff Current (V _{CB} = Rated, T _A = 25°C) (V _{CB} = Rated, T _A = 100°C)	I_{CBO1}	—	1.0	—	μA
	I_{CBO2}	—	50	—	
Emitter Cutoff Current (V _{EB} = 6 V)	I_{EBO}	—	1.0	—	μA
DC Current Gain * (I _C = 1 mA, V _{CE} = 10 V) (I _C = 25 mA, V _{CE} = 10 V) (I _C = 100 mA, V _{CE} = 10 V)	H_{FE}	20	250	—	
		40	300	—	
		20	250	—	
Collector-Emitter Saturation Voltage * (I _C = 25 mA, I _B = 2.5 mA)	V_{CE(SAT)}	—	500	—	mV
Base-Emitter Saturation Voltage (I _C = 25 mA, I _B = 2.5 mA)	V_{BE(SAT)}	—	1.0	—	Volts
Current Gain Bandwidth Product * (I _C = 10 mA, V _{CE} = 10 V, f = 10 MHz)	f_T	25	—	—	MHz
Output Capacitance V _{CB} = 20 V, I _E = 0 A, f = 1.0MHz	C_{ob}	—	10	—	pF
Turn on Delay Time Rise Time Storage Time Fall Time V _{CC} = 100 V I _C = 100 mA I _{B1} = I _{B2} = 10 mA	T_d	—	500	—	ns
	T_r	—	1200	—	ns
	T_s	—	2.0	—	μs
	t_f	—	500	—	ns

Notes: * Pulse Test: Pulse Width = 300 μs. Duty Cycle = 2%.
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PIN ASSIGNMENT (Standard)			
Package	Collector	Emitter	Base
4 Pin CLCC (-4)	Pin 1	Pin 2	Pin 3
TO-5 (/5)	Pin 3	Pin 1	Pin 2
CERPACK (G)	CASE	Pin 1	Pin 2
SMD.22	Pin 1	Pin 2	Pin 3

FIGURE 1 – CASE OUTLINES

